

*AMENDMENTS TO THE CLAIMS*

This listing of claims replaces all prior versions, and listings, of claims in the application.

1. (Previously Presented) A semiconductor integrated circuit device comprising:  
a resonant circuit resonating at an arbitrary frequency;  
a transmission line for transmitting a high-frequency signal having the frequency,  
wherein a first end of said transmission line is connected to said resonant circuit;  
an active element having a first electrode connected to a second end of said  
transmission line, a second electrode which is grounded through a reactance element, and  
a third electrode;  
an output-matching circuit including a diode section for regulating an oscillation  
power and a high-frequency signal output terminal, wherein a first end of said diode  
section is connected to said third electrode of said active element, and said high-  
frequency signal output terminal is connected to a second end of said diode section; and  
a substrate having a main surface on which said resonant circuit, said transmission  
line, said active element, and said output-matching circuit are arranged.
2. (Previously Presented) The semiconductor integrated circuit device according  
to claim 1, wherein said diode section includes a plurality of diodes connected in an  
inverse parallel arrangement.
3. (Withdrawn) The semiconductor integrated circuit device according to claim 1,  
wherein said diode section includes a plurality of diodes connected in series.
4. (Withdrawn) The semiconductor integrated circuit device according to claim 1,  
further comprising a bias circuit for applying a DC bias to said diode section.

Claims 5-8 (Cancelled).